Resonant waveguide device with vertical gratings

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Transmission resonant filters in a waveguide with vertical gratings have been realized in silic on on insulator wafers. Experimental studies of fabricated devices show a broad stopband of ~19 nm in the center of which exists a narrow transmission band of ~0.5 nm with a quality factor of ~3000. These resonant cavities are useful for laser cavities, switches, modulators, detectors, and tunable filters. © 2007 Optical Society of America


The distributed Bragg reflector (DBR) in planar waveguide technology has been used to perform and enhance various functionalities of optical elements such as single-mode selectors in semiconductor lasers, optical filters, switches, modulators, couplers, detectors, and sensors.1-5 A DBR structure exhibits in its transmission spectrum a stopband centered at the Bragg wavelength, where the bandwidth of the stopband is determined by the amplitude of the periodic index modulation and the Bragg wavelength is determined by the mean period of the index modulation. Many devices use a quarter-wavelength phase shift embedded in the middle of a DBR structure to construct a highly resonant cavity and create a narrow resonant transmission band in the middle of the stopband at the Bragg wavelength.6-8 The DBRs conventionally fabricated on the surface of the waveguide involve an additional procedure separate from the waveguide.1-5 In contrast, we exploit a method to define the DBRs and nanostructured resonant devices by using corrugation of waveguide sidewalls. This method was first developed to create periodic corrugations of single-mode distributed feedback lasers and distributed reflector lasers.6-8 In this letter, we extend this approach to implement passive transmission resonant filters by using a silicon on insulator (SOI) material system.

We consider the schematic structure of the resonant transmission filter, where vertical gratings with full depth of single side (∆W̄_S) are engraved on both sidewalls of the waveguide with the average width (W_S). It is assumed that a 250-nm-thick silicon core is surrounded by silicon dioxide. A pair of Bragg reflectors each of length (L) and period (Λ) is separated by a half-period (Λ/2). For the transverse electric (TE) fundamental mode, where the electric field is parallel to the wafer surface, the coupling coefficient (κ) for the first-order vertical grating is given by

\[ \kappa = \Gamma \left( \frac{\pi \Delta W_S n_S^2 - n^2}{W_{eff} n q} \right) \left[ \frac{n^2}{n_S^2} - \frac{n^2}{n_{SiO_2}^2} + 1 \right], \]

where \( n = \beta / k \) is the effective index of the guided mode with the propagation constant \( \beta \) and the wave-number in vacuum \( k \); \( n_S \) is the effective index of the symmetric slab waveguide,9 where the refractive indices of the silicon core layer and silicon dioxide cladding layers (n_{SiO_2}) are assumed to be 3.5 and 1.4, respectively; \( \Gamma \) is a fraction of the TE mode confined in the silicon core (~85% for this study)10; \( q = (n/n_S)^2 + (n/n_{SiO_2})^2 - 1 \); and effective width \( W_{eff} = W_S + 2/(q \gamma) \) with \( \gamma = (2 - k^2 n_{SiO_2}^2)^{1/2} \). Equation (1) indicates that \( \kappa \) is linear in \( \Delta W_S \), whereas the corresponding Bragg length (L_B = 1/\kappa) is inversely proportional to \( \Delta W_S \). We construct a resonant waveguide of \( W_S = 500 \) nm with values of \( \Delta W_S = 50, 75, 100 \) nm, corresponding to \( \kappa \) of ~600, 900, and 1200 cm\(^{-1} \) at \( \lambda = 1550 \) nm.

Next, consider a Fabry–Perot (FP) type filter made from a pair of such identical Bragg reflectors, each having reflection (r) and transmission amplitude (t) coefficients and separated by a spacer of length \( d = \Lambda / 2 \), causing a phase shift (\( \phi = \pi / 2 \)). The transmission amplitude of the resonant filter (t_{RF}) as a function of \( \lambda \) is given by

\[ t_{RF} = \frac{t^2 \exp(i\phi)}{1 - r^2 \exp(2i\phi)}, \]

where \( t = 1/[(\cosh(\mu L) - (i\delta - \alpha/2)|\sinh(\mu L)|/\mu] \), \( r = -i\kappa/|\sinh(\mu L)/\mu| \), \( \mu^2 = \mu^2 + (i\delta - \alpha/2)^2 \) with detuning parameter \( \delta = \beta - \beta_B - (d/\partial \omega)(\omega - \omega_B) = (\omega - \omega_B)/v_g \), \( \alpha \) is the loss of Bragg reflector, \( \omega \) is the angular frequency, \( \omega_B = 2\pi c/\lambda_B \) is the Bragg angular frequency, \( v_g = (c/n_g) \) is the group velocity of the waveguide mode, \( c \) is the speed of light in vacuum, \( \lambda_B = 2n\lambda \) is the Bragg wavelength, and \( n_g = \left[ n - n_B(\Delta n/\Delta \lambda) \right] \) is the group index of the waveguide mode.2,5 Figure 1 shows the simulated results of transmitted power, [t_{RF}]^2, as a function of the deviation from \( \lambda_B \). In the simulation, we used \( n_g = 3.8 \) and \( \kappa \) values calculated at \( \lambda_B = 1550 \) nm. We determined the value of \( n_g = 3.8 \pm 0.1 \) by measuring FP resonant mode spacing of a straight waveguide with \( W_S = 500 \) nm at \( \lambda = 1550 \) nm. The black, blue, and red lines correspond to \( \kappa = 600, 900, \) and 1200 cm\(^{-1} \); \( \alpha = 10, 20, \) and 30 cm\(^{-1} \); and \( L = 70 \) μm (2.1 x L_B), 50 μm (2.25 x L_B), and 40 μm (2.4 x L_B), respectively.

The designed devices are fabricated on a ~0.5 cm\(^2 \) size of 15.24 cm SOI wafer consisting of a silicon top layer with a mean thickness of 252.2 nm with a distribution of 6.8 ~ 18.3 nm on a ~3-μm-thick silicon di-
oxide layer. Polymethylmethacrylate with 950 K molecular weight is spin-coated on the sample and baked, resulting in \( \sim 200 \) nm thickness. A scanning electron microscope (SEM) equipped with a 16 bit digital-to-analog converter and pattern generation software is used to pattern the whole structure at an acceleration voltage of 40 kV. Following a standard lift-off process using \( \sim 20 \) nm-thick nickel, the silicon layer is selectively etched in a reactive ion etcher using a mixture of \( \text{BCl}_3/\text{Ar} \) with the following conditions: gas flow rates \( \text{BCl}_3/\text{Ar} = 10/10 \text{ SCCM} \), pressure \( \sim 30 \) mTorr, power density \( \sim 0.1 \) W/cm\(^2\), and temperature \( \sim 20^\circ\text{C} \). This results in an etching rate of \( \sim 75 \) nm/min for a sample size of \( \sim 1 \times 0.5 \) cm\(^2\). The choice of a \( \text{BCl}_3/\text{Ar} \) mixture enables us to use the buried oxide layer as an etching stop layer. After chemically removing nickel, an \( \sim 1 \) \( \mu \)m-thick buffer layer of silicon dioxide is sputtered on the whole structure. After cleaving of the facets of the device, an antireflection coating \( \text{Si}_3\text{N}_4 \) is sputtered to reduce additional FP resonance due to the cleaved facets. A tilted SEM image of the fabricated vertical grating is shown in Fig. 2(a). Magnified views are displayed in the insets of Fig. 2(a).

Optical power should be delivered from the fiber to the filters. Our SEM-based lithography system has only \( 90 \times 90 \) \( \mu \)m\(^2\) of writing area, with resolution sufficient for patterning of the vertical gratings. It is well known that, when the waveguide width is tapered or expanded over a certain length, its guided mode also changes adiabatically. The adiabatic mode matching can be used to transfer a tightly confined waveguide mode to a larger size mode for efficient coupling with optical fiber.\(^{11,12}\) Here, we apply this concept for interconnection of waveguides patterned at different magnifications. In a \( 90 \times 90 \) \( \mu \)m\(^2\) area, the remaining length of \( \sim 20 \) \( \mu \)m from the longest filter length of 70 \( \mu \)m is assigned to expand the width from 500 nm to 1.5 \( \mu \)m in each end (\( \sim 10 \) \( \mu \)m). Without moving the sample and changing other microscope settings, we first fabricate the patterns in a \( 90 \) \( \mu \)m\(^2\) writing area at 1000\( \times \) magnification and then 2 \( \mu \)m wide waveguides in \( 300 \times 300 \) \( \mu \)m\(^2\) at 300\( \times \). Pattern displacements at the boundaries of the two writing areas are measured from SEM inspections. The displacements are then corrected by shifting the design of 2 \( \mu \)m wide waveguide patterns. We have empirically found that \( \sim 200 \) nm placement accuracy can be routinely obtained without repetitions. Figure 2(b) shows a micrograph of the whole device, and the inset shows the magnified view of the tapered waveguide connections.

For testing, a TE-polarized tunable laser source is coupled into polarization-maintaining tapered fiber with an output spot diameter of \( \sim 2.5 \) \( \mu \)m, producing \( \sim 20 \) dB polarization extinction. Another polarization-maintaining tapered fiber is used to collect light from the fabricated devices and its relative power transmission over the wavelength is analyzed. Figure 3 shows the measured transmission spectra, which are in good agreement with the calculated prediction shown in Fig. 1. Oscillatory behavior outside of the stopband and a slight asymmetry of the resonant transmission band are most likely due to residual reflections on the two \( \text{Si}_3\text{N}_4 \)-coated facets. Comparison of Figs. 1 and 3(a) indicates that Eq. (1) along with Eq. (2) predicts the result with good accuracy in \( \Delta W_S/W_S = 10\% \). Comparison of Figs. 1 and 3(b) shows that as \( \Delta W_S/W_S > 10\% \), Eq. (1) tends to start overes-

![Fig. 1. (Color online) Simulated plots of transmitted power from the devices.](image)

![Fig. 2. SEM micrographs of the devices. The insets show magnified views of the rectangles: (a) Transmission resonant filter with vertical gratings. (b) Micrograph of the whole device and its inset showing the waveguide connection defined at two different magnifications. The dotted rectangle shows the area defined at 1000\( \times \) magnification.](image)
alized for what is believed to be the first time. Bragg reflectors are constructed by engraving vertical gratings with 10–20% modulation depth of their waveguide width on both sidewalls of a 500-nm-wide waveguide. Transmission resonant filters are created by introducing a half-period offset into a pair of Bragg reflectors with vertical gratings. The measured transmission spectrum of the fabricated device shows a wide stopband of \( \sim 19 \text{ nm} \), in the center of which exists a narrow transmission band of \( \sim 0.5 \text{ nm} \) with a quality factor \( Q = \lambda_0 / \Delta \lambda \sim 3000 \).

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